PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PRACE No. 100/051

Serial No.: 09/851,274

Filed: May 8, 2001

Confirmation No.: 3436

Art Unit: 1752

Examiner: Lee, Sin J. RESIST MATERIAL AND METHOD FOR PATTERN FORMATION

Commissioner for Patents Washington, DC 20231

Date: January 6, 2003

AMENDMENT

Sir:

This Amendment is responsive to the Office Action mailed on September 6, 2002, and is submitted with the requisite fee for a one-month extension for response. A marked-up version of the claims showing changes made to the claims is attached hereto and is entitled "VERSION WITH MARKINGS TO SHOW CHANGES MADE."

In the Claims:

Please amend Claims 1, 2, and 13 as follows:

- 1. (Amended) A resist material comprising one or more surfactants having a fluorine substituent and between 10 and 2000 ppm of a non-ionic surfactant comprising one or more non-ionic surfactants having neither a fluorine substituent nor a silicon-containing substituent.
- 2. (Amended) A resist material according to claim 1 wherein said non-ionic surfactant is one or more compounds selected from the group consisting of polyoxyalkylene alkyl ether esters, polyoxyalkylene alkyl ether, polyoxyalkylene dialkyl ether, polyoxyalkylene aralkyl alkyl ether, polyoxyalkylene aralkyl ether, polyoxyalkylene diaralkyl ether, and polyoxyalkylene laurylates.
- 13. (Amended) A method for forming a pattern on a substrate comprising: coating a resist material on a substrate, the resist material comprising one or more surfactants having a fluorine substituent and between 10 and 2000 ppm of a non-ionic surfactant comprising one or more non-ionic surfactants having neither a fluorine substituent nor

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